English Times la diori

(11)Publication number:

55-163868

(43)Date of publication of application: 20.12.1980

(51)Int.CI.

HO1L 23/48

(21)Application number

(22)Date of filing:

54-071117 08.06.1979 (71)Applicant: (72)Inventor:

FUJITSU LTD

AOKI TSUYOSHI

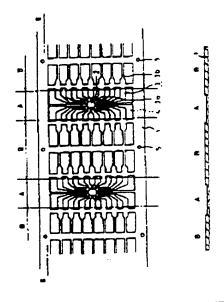
KUBOTA AKIHIRO YAMAUCHI OSAMU SUGIURA RIKIO

(54) LEAD FRAME AND SEMICONDUCTOR DEVICE USING THE SAME

(57)Abstract:

PURPOSE: To enhance the strength of an external connector in a lead frame of a resin molded semiconductor device and increase the density of a chip connector by forming thin chip carrying base of the lead frame and thin lead terminal formed therearound and thick external connecting lead

CONSTITUTION: A guide hole 5 is perforated at a metallic plate, and thin and thick portions A and B are formed by pressing. Then, a chip carrying base 2 and a lead terminal 3 are formed on the lead frame 1 by stamping. The semiconductor chip is carried on a chip carrying base 2, wire bonded to the lead terminal 3, and clamped from both front and rear surfaces of the molding frame, resin is filled to seal the semiconductor device.



LEGAL STATUS

[Date of request for examination]

[Date of sending the examiner's decision of rejection]

[Kind of final disposal of application other than the examiner's decision of rejection or application converted registration)

[Date of final disposal for application]

[Patent number]

[Date of registration]

[Number of appeal against examiner's decision of rejection]

[Date of requesting appeal against examiner's decision of rejection]

[Date of extinction of right]

Copyright (C): 1998,2000 Japan Patent Office

LEAD FRAME AND SEMICONDUCTOR DEVICE USING THE SAME

Patent Number:

JP55163868

Publication date:

1980-12-20

Inventor(s):

AOKI TSUYOSHI; others: 03

Applicant(s):

FUJITSU LTD

Application Number: JP19790071117 19790608

Priority Number(s):

IPC Classification: H01L23/48

EC Classification:

Equivalents:

Abstract

PURPOSE:To enhance the strength of an external connector in a lead frame of a resin molded semiconductor device and increase the density of a chip connector by forming thin chip carrying base of the lead frame and thin lead terminal formed therearound and thick external connecting lead terminal. CONSTITUTION: A guide hole 5 is perforated at a metallic plate, and thin and thick portions A and B are formed by pressing. Then, a chip carrying base 2 and a lead terminal 3 are formed on the lead frame 1 by stamping. The semiconductor chip is carried on a chip carrying base 2, wire bonded to the lead terminal 3, and clamped from both front and rear surfaces of the molding frame, resin is filled to seal the semiconductor device.

Data supplied from the esp@cenet database - 12